



TIP142T TIP147T

COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

- STM PREFERRED SALESTYPES
- COMPLEMENTARY PNP - NPN DEVICES
- MONOLITHIC DARLINGTON CONFIGURATION
- LOW VOLTAGE
- HIGH CURRENT
- HIGH GAIN

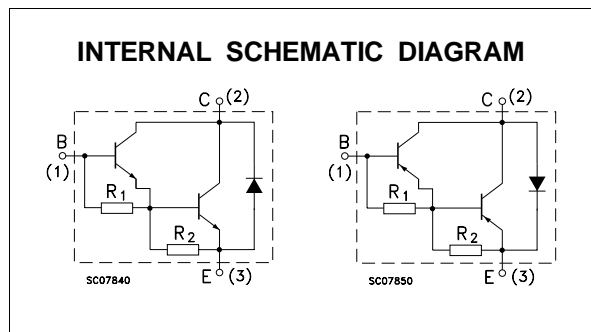
APPLICATIONS

- GENERAL PURPOSE SWITCHING

DESCRIPTION

The TIP142T is a silicon epitaxial-base NPN power transistor in monolithic Darlington configuration, mounted in TO-220 plastic package. They are intended for use in power linear and switching applications.

The complementary PNP type is TIP147T.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		NPN	TIP142T	
		PNP	TIP147T	
V_{CBO}	Collector-Base Voltage ($I_E = 0$)		100	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)		100	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)		5	V
I_C	Collector Current		15	A
I_{CM}	Collector Peak Current ($t_p < 5ms$)		20	A
I_B	Base Current		0.5	A
P_{tot}	Total Dissipation at $T_{case} \leq 25^\circ C$		90	W
T_{stg}	Storage Temperature		- 65 to 150	$^\circ C$
T_j	Max. Operating Junction Temperature		150	$^\circ C$

For PNP types voltage and current values are negative.

TIP142T / TIP147T

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	1.38	°C/W
-----------------------	----------------------------------	-----	------	------

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
I _{CBO}	Collector Cut-off Current (I _E = 0)	V _{CB} = 100 V				1	mA
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CE} = 50 V				2	mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V				2	mA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 30 mA		100			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 5 A	I _B = 10 mA			2	V
		I _C = 10 A	I _B = 40 mA			3	V
V _{BE(on)} *	Base-Emitter Voltage	I _C = 10 A	V _{CE} = 4 V			3	V
h _{FE} *	DC Current Gain	I _C = 5 A	V _{CE} = 4 V	1000			
		I _C = 10 A	V _{CE} = 4 V	500			
t _{on} t _{off}	RESISTIVE LOAD						
	Turn-on Time	I _C = 10 A	I _{B1} = 10 mA		0.9		ms
	Turn-off Time	I _{B2} = -40 mA	R _L = 3 Ω		4		μs

For PNP types voltage and current values are negative.

* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a trademark of STMicroelectronics

© 1998 STMicroelectronics – Printed in Italy – All Rights Reserved
STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - France - Germany - Italy - Japan - Korea - Malaysia - Malta - Mexico - Morocco - The Netherlands -
Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A.